

# Quantum phase transitions in two-dimensional systems

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Experimental data on quantum phase transitions in two-dimensional systems (superconductor-insulator, metal-insulator, and transitions under conditions of integer quantum Hall effect) are critically analyzed.

## I. INTRODUCTION

Currently there are quite a few reviews and even books (see, e.g., Refs.<sup>(1,2,3,4,5,6,7,8,9)</sup>), devoted to quantum phase transitions, where the main focus is on theoretical ideas, while experimental data are used for illustrative purposes only. The goal of the present review is to give a critical analysis of the experimental data on quantum phase transitions in two-dimensional systems, which is aimed at revealing reliable established facts, formulating directions for future research and determining unresolved problems.

It is convenient to start the explanation of the nature of quantum phase transitions from continuous phase transitions, i.e., those not having a stationary coexistence of the two distinct phases (and, therefore, not having stationary phase boundaries either). Thereby, at the continuous phase transition point the system as a whole is changing its phase state. This change of the phase state is brought into relation with an order parameter which is finite in one of the phases and permanently becomes zero at the transition point. Finding an appropriate order parameter for some particular phase transition often presents a nontrivial problem in itself. After transition the system becomes stationary and homogeneously disordered one. Therefore, for all continuous transitions, as the transition point is approached, diverge both the duration  $\tau_c$  and characteristic size  $r_c$  of the fluctuations of the order parameter.

The class of continuous phase transitions includes continuous thermodynamic phase transitions, (e.g., second order phase transitions) characterized by singularities in the temperature derivatives of thermodynamic potentials. The latter are caused by thermal fluctuations in the system. The divergence of the density fluctuations size in carbon dioxide ( $CO_2$ ) in the vicinity of a critical point, corresponding to the continuous thermodynamic phase transition, was for the first time experimentally established in<sup>10</sup> by observing a refraction of a visible light on the density fluctuations.

One can imagine continuous phase transitions to occur at zero temperature as well. The variation of the system's state is, in this case, not related to the changing temperature, but to the variation of a certain external parameter (magnetic field, doping level, material composition, etc.). At zero temperature it is, of course, impossible to register a phase transition through singularities in the temperature derivatives of thermodynamic potentials, therefore

one should exploit some other properties of the system, for example, its kinetic characteristics, in order to find it.

Repeated measurements of a physical quantity with an operator not commuting with Hamiltonian of the system lead, even for a system in a stationary state and at arbitrary low temperature, to different results: the measured quantity experiences quantum fluctuations. In many measurements one can evaluate dispersion, and in periodic measurements, the spectral density of states. Both of these values are determined by the energy of the excited quantum states of the system. At finite temperature, exceeding the characteristic energy between stationary states, the main reason for getting different results in repeated measurements is the considerable probability of finding the system in different stationary states, i.e., the thermal fluctuations. For temperatures about characteristic energy between stationary states both types of fluctuations are equally important.

At zero temperature only quantum fluctuations of the order parameter could drive the phase transition. If tuning parameter reaches its critical value:  $K = K_c$ , the system homogeneously changes the ground state after quantum fluctuation of diverging size and zero frequency, thus experiencing a quantum phase transition.

At first glance one might get the impression that quantum phase transitions cannot be studied experimentally and do not have practical importance because of impossibility to reach zero of the temperature. In reality, in the range of temperatures in which quantum fluctuations compete with thermal ones, and at values of the tuning parameter close to the critical one, a behavior of the system is expected to show special features signaling the existence of a zero temperature quantum phase transition.

Let us consider, for example, a quantum phase transition located at the zero-temperature end of the second order phase transition curve (Fig. 1). At finite fixed temperature the increase of the tuning parameter  $K$  leads to a second order phase transition at the intersection with the solid line in Fig. 1. The state of the system is changed through thermal disordering, i.e., there is a transition from the ordered to the thermally disordered state. This phase transition is only real phase transition observed at finite temperature.

At zero temperature, we expect a quantum phase transition from ordered to disordered state when the external tuning parameter reaches its critical value  $K_c$ . As a tran-

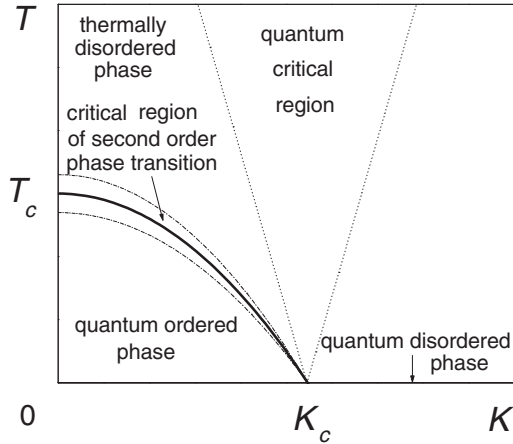


FIG. 1: A diagram of second-order phase transition.  $K = K_c$ , and  $T = 0$  is the quantum phase transition point. The dotted lines indicate the boundaries of the quantum critical region.

sition should occur simultaneously in the whole system, we have to conclude that at the phase transition point the critical frequency of quantum fluctuations  $\tau_c^{-1}$ , corresponding to the energy gap between the ground state of the system and its lowest excited state, should tend to zero. Simultaneously, the spatial length of fluctuations  $r_c$  (correlation length) should tend to infinity.

Let us return to the case of finite temperature. Because the critical frequency and correlation length of quantum fluctuations are temperature-independent, we can mark, in the  $(K, T)$  plane, the lines on which the critical frequency  $\tau_c^{-1}$  of quantum fluctuations equals the temperature  $kT/\hbar$ . These lines shown by the dotted lines in Fig. 1 border the so-called quantum critical region, in which the characteristic length of coherent quantum fluctuations is less than the correlation length  $r_c$  and is restricted by the temperature. At fixed temperature, a crossover from the thermally disordered to the quantum disordered state takes place as this region is intersected. The observed continuous variation of properties in the quantum critical region is reminiscent of the quantum phase transition.

Thereby, the motion parallel to X-axis in Fig. 1 corresponds, consequently, to a continuous phase transition, characterized by its own correlation length of order parameter fluctuations and attached to the solid line in the figure, and to subsequent gradual change in the kinetic characteristics of the system in the quantum critical region. The width of this region near  $K_c$  is dependent on the temperature.

There are systems in which the existence of the quantum ordered phase is assumed at zero temperature only. Such a system has a quantum ordered state at  $T = 0$ ,  $K < K_c$ , experiencing a quantum phase transition at

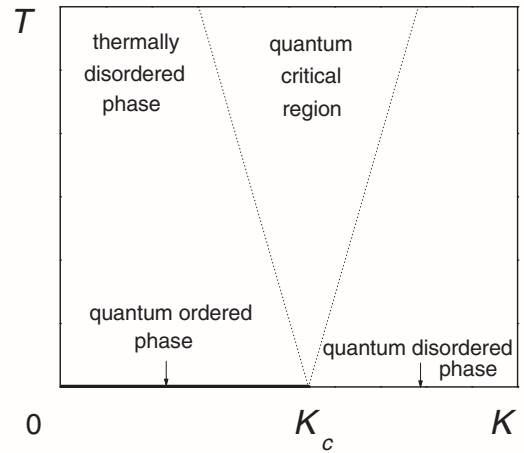


FIG. 2: Phase diagram of a system experiencing a quantum phase transition at  $K = K_c$ ,  $T = 0$ . The dotted lines indicate the boundaries of the quantum critical region.

$K = K_c$ . At finite temperatures this system is disordered (Fig. 2). Again, the moving parallel to X-axis in Fig. 2 leads to a consequent observation of the thermally disordered phase, to a gradual change in its properties towards those characteristic of quantum disorder and, further, beyond the boundaries of the quantum critical region, to the observation of properties peculiar to the quantum disordered state.

In experiments, the interval of temperatures available for studying of the transition region properties is principally restricted from above and below. In the low temperature limit, a continuous phase transition takes place at  $K \approx K_c$ . In this case, when moving along horizontal line in Fig. 1, the critical region of the second order phase transition is inseparable from the quantum critical one. A restriction at high temperatures is related to the fact that the correlation length cannot be arbitrarily small and is restricted by characteristic scales of the problem (coherence length, mean free path, etc.).

In the quantum critical region, a continuous change of thermodynamic and kinetic properties occurs. Characteristics of the system are the functions of only one scaling variable  $u$ , namely the ratio of the correlation radius  $r_c$  to the temperature-assigned dephasing length  $L_\Phi \propto T^{-1/z}$ , where  $z$  is the so-called dynamic critical index. Assuming that in the vicinity of the phase transition point the correlation radius diverges as  $r_c \propto |K - K_c|^{-\nu}$ , the scaling variable can be written in the form

$$u = |K - K_c|/T^{1/y}, y = z\nu, \quad (1)$$

where  $\nu$  is the critical index of the correlation radius. In other words, in the quantum critical region one expects that kinetic characteristics (for example, resistance) will

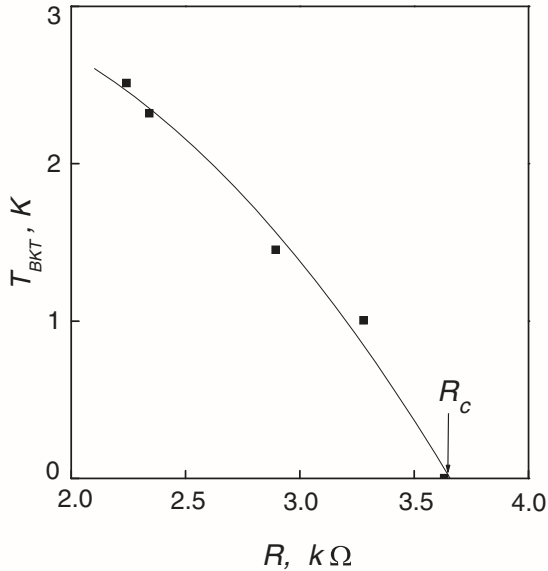


FIG. 3: Temperature of BKT phase transition,  $T_{BKT}$ , as a function of the disorder degree of an  $In/InO_x$  film 10 nm thick. As a measure of disorder in the film, its resistance per unit surface area at room temperature has been chosen<sup>16</sup>.

be of the form

$$R = R_0 f\left(\frac{|K - K_c|}{T^{1/y}}\right). \quad (2)$$

A competition of quantum and classical fluctuations can also be defined by the ratio of the frequency of critical quantum fluctuations to the temperature. Using this ratio leads, of course, to the same scaling parameter  $u$  and equation (2).

In most experimental papers, an observation of the scaling relation similar to equation (2) was considered as a strong evidence for the quantum phase transition, although in some publications<sup>11,12</sup> the remark was made that in restricted temperature range the occurrence of such a relation can be accidental.

A behavior typical for quantum phase transition can be observed in a number of two-dimensional systems. There are the superconductor-insulator and metal-insulator transitions as well as transitions between different quantum states in quantum Hall effect regime. Below we present the short review of experimental publications in this field.

## II. SUPERCONDUCTOR-INSULATOR PHASE TRANSITION IN THIN FILMS

Decreasing one of the sizes of a superconducting sample  $d \ll \lambda$  ( $\lambda$  is the penetration length of the magnetic field into massive sample) lowers the transition temperature to resistive state. The decrease of this temperature, caused by the enhanced role of thermal fluctuations in two-dimensional systems, was first predicted by

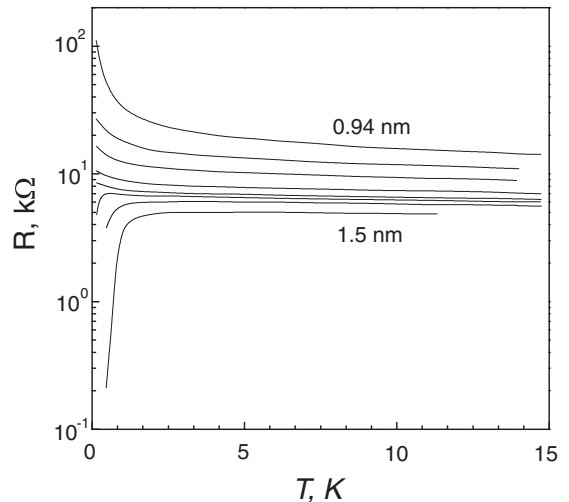


FIG. 4: Temperature dependencies of resistance per unit surface area of amorphous  $Bi$  films of varying thickness  $d = 0.94 \div 1.5$  nm, changing with the step of 0.08 nm (according to the data of Ref.<sup>[17]</sup>).

V L Beresinskii<sup>13</sup> and theoretically investigated in Refs [14,15]. Since then a similar continuous phase transition in thin films of superconductors is known as Beresinskii-Kosterlitz-Thouless transition (BKT). In the absence of an external magnetic field the vortices in thin superconducting film are generated by thermal fluctuations. It is energetically favorable for vortices with opposite circulation to form bound pairs. At low enough temperature  $T < T_{BKT}$ , the 'vortex-antivortex' pairs are stable and a film is in the superconducting state. A temperature increase up to the critical one,  $T = T_{BKT}$ , leads to dissociation of 'vortex molecules' accompanied with the continuous phase transition of a superconducting film to a resistive state. The temperature of the BKT phase transition decreases with increasing disorder in the film. The resistance of the film can be considered as a measure of its disorder. Dependence of  $T_{BKT}$  on the disorder degree is shown in Fig. 3. Films with a resistance smaller than the critical one,  $R_c$ , experience BKT transition, but for  $R > R_c$  the film is still in the resistive state up to the lowest experimentally reachable temperatures.

BKT phase transition can be driven by the change of another external parameter, e.g., the film thickness or magnetic field. In Fig. 4, temperature dependencies of the resistance of amorphous bismuth films of varying thickness  $d = 0.94 \div 1.5$  nm are presented. The films having a critical thickness  $d_c \simeq 1.3$  nm have an approximate temperature-independent value of resistance  $R_c \simeq 7$  kOhm. In the low-temperature range, films having a thickness exceeding the critical one exhibit a positive derivative  $dR/dT > 0$  characteristic of metallic conductivity and, with further temperature decrease, expe-

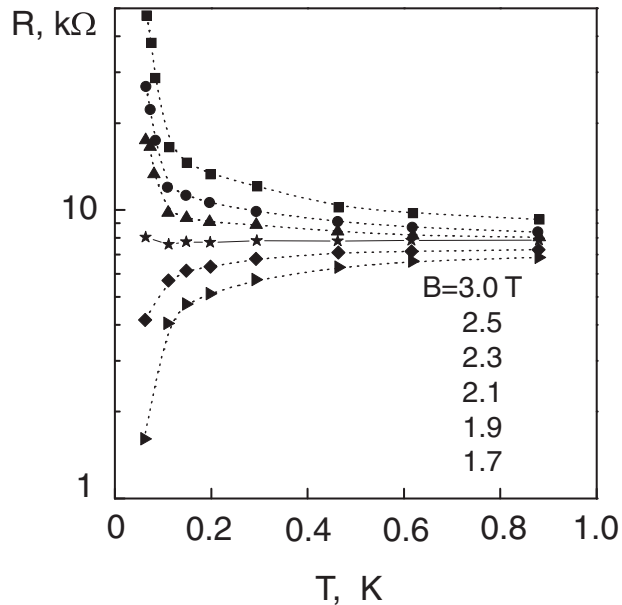


FIG. 5: Temperature dependencies of the resistance of an amorphous *InO* film with thickness  $d = 20$  nm, measured at different magnetic fields  $B = 1.7 \div 3.0$  T (according to the data of Ref.<sup>[18]</sup>).

rience a transition to the superconducting phase. Films having a thickness less than the critical one show, however, a negative derivative  $dR/dT < 0$ . A decrease in the film's thickness down to  $d \approx 0.9$  nm increases its resistance up to  $\sim 10^4$  kOhm. Therefore, films having a thickness  $d < d_c$  show quasi-insulating properties without experiencing the BKT transition.

The magnetic field has an analogous influence on BKT phase transition. Isomagnetic curves for the temperature dependence of resistance of amorphous *InO* film ( $d = 20$  nm) in the magnetic fields  $B = 1.7 \div 3.0$  T, are shown in Fig. 5. The temperature-independent value of the film's resistance  $R_c \approx 8$  kOhm corresponds to the critical magnetic field  $B_c \approx 2.1$  T. For magnetic fields lower than the critical one, the film shows a positive temperature coefficient of resistance  $dR/dT > 0$  typical for metallic state. At lowering the temperature the film with metallic conductivity demonstrates the transition into superconducting state (see Fig. 5). For magnetic fields larger than the critical one, the film exhibits quasi-dielectric properties with a negative derivative  $dR/dT < 0$  and no signs of its transition to the superconducting state can be observed down to the temperature  $T = 0.035$  K.

Therefore, the available experimental data allow us to conclude that when an external parameter (film thickness, degree of disorder, magnetic field) reaches its criti-

cal value at zero temperature, the ground state of the film changes in a fundamental way: from the superconducting state to the insulating state. In other words, a thin film undergoes the quantum phase transition from superconducting to insulating state at  $K = K_c$ . The pioneering paper<sup>[19]</sup> provides a theoretical ground for quantum superconductor-insulator phase transition in thin films.

A quantum superconductor-insulator transition can be considered as the quantum analogue of continuous BKT phase transition. At absolute zero of the temperature, the vortices arising in a thin film due to quantum fluctuations are localized ('pinned' by the defects) and form so called 'vortex glass'. Strengthening the external magnetic field increases the concentration of vortices with orientation corresponding to that of the field. The growth of the disorder degree in the film (or decrease of its thickness) also increases the concentration of the vortices. When a concentration of vortices approaches its critical value, the localization length of vortices diverges as a function of  $|K - K_c|$ . Finally, at the critical value of the external parameter  $K = K_c$ , the vortices delocalize. As shown in Ref.<sup>[19]</sup>, delocalization of vortices is necessarily accompanied by the localization of Cooper pairs, thus leading to the formation of the so-called 'Cooper pair glass'. Such 'complementarity' in the behavior of two boson systems is due to the duality of their Hamiltonians in a two-dimensional film<sup>[19]</sup>. At zero temperature, a localization of Cooper pairs means the transition from superconducting to insulating state. The metallic state, in which Cooper pairs and vortices move diffusively with a finite resistance, is an intermediate one in between the insulating and superconducting states at absolute zero of the temperature.

As an example, let us consider magnetic-field-induced transition of an amorphous *InO* film with thickness  $d = 20$  nm from superconducting to insulating state<sup>20</sup>. These films are two-dimensional for vortices, because the penetration length of the magnetic field is  $\lambda \geq 100$  nm. However, for normal electrons the *InO* film is a bulk sample, because the electron mean free path in the film is  $l \sim 1$  nm. Experimental dependencies of the resistance of such a system on the normal to the film's surface magnetic field are shown in Fig. 6<sup>a</sup> for various temperatures. The temperature-independent value of the resistance  $R_{cn} \approx 8$  kOhm corresponds to the critical magnetic field  $B_{cn} \approx 2.2$  T. At a finite temperature, the magnetic field value at which the film resistance becomes finite corresponds to the transition to resistive state or BKT transition (see Fig. 7). The boundary of BKT phase transition in Fig. 7 is determined from the film resistance exceeding 1/1000 of its maximal value in the resistive state. The boundaries of quantum critical region at an arbitrary temperature,  $B(T)$ , can be determined from the coincidence of resistance measured at the maximal temperature in the experiment,  $T = T_{max}$ , with that corresponding to the temperature  $T$ , after normalizing of the resistance according to  $R(B) = R^{norm}((B - B_{cn}) * (T_{max}/T)^{1/z\nu})$ . The thus found boundaries of the quantum critical region

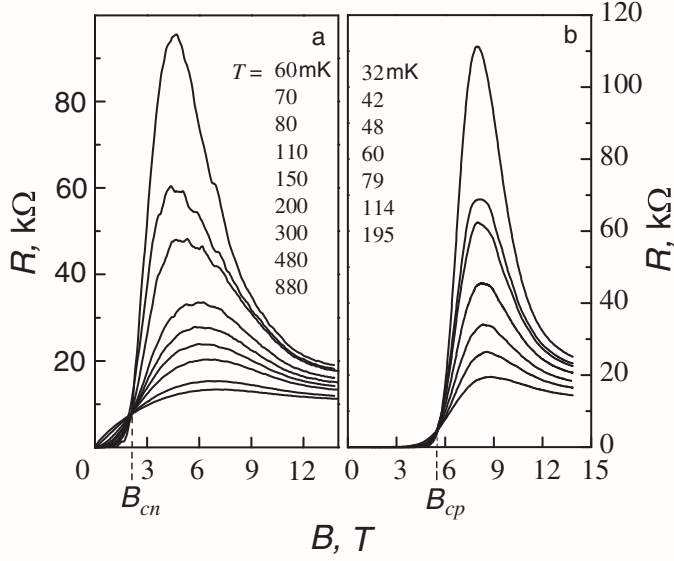


FIG. 6: Transition of amorphous *InO* film with thickness  $d = 20$  nm from the superconductive to the resistive state<sup>20</sup>. The film resistance is shown as a function of the external magnetic field having (a) normal, and (b) parallel orientation in the temperature range  $T = 32 \div 880$  mK. Dashed lines mark the critical values of the magnetic field, corresponding to the quantum superconductor-insulator phase transition.

in the temperature range  $T = 60 \div 480$  mK are shown in Fig. 7 by circles and triangles.

The phase diagram of BKT phase transition in the normal magnetic field (see Fig. 7) is qualitatively similar to the theoretical model, presented in Fig. 1. There exists, however, difference in the sign of the second derivative of the BKT phase transition temperature in the plane  $(B, T)$ . According to the model ideas<sup>19</sup>, the BKT phase transition temperature changes as  $T_{BKT} \propto (B_c - B)^{0.5}$  with a negative second derivative (see Fig. [1]). Experimentally, however, this second derivative is positive and does correspond to  $T_{BKT} \propto |B - B_{cn}|^{2.49}$ .

Let us now discuss the phase boundaries of quantum critical region in  $(B, T)$  plane. In Refs.<sup>[18,20]</sup>, it was shown that in the quantum critical region the resistance of amorphous *InO* films in the normal magnetic field is a function of the scaling variable  $u \propto |B - B_{cn}|T^{-1/\nu}$  with exponent  $z\nu = 1.15 \div 1.22$ . The value of the product  $z\nu$  of critical indices obtained in Refs.<sup>[18,20]</sup> is not universal. It was found, e.g., for amorphous *InO<sub>x</sub>* and *MoGe* films  $z\nu = 1.26 \div 1.31$ <sup>21</sup> and  $1.27 \div 1.37$ <sup>22</sup>, correspondingly. In amorphous and granular *In* films  $z\nu = 0.48 \pm 0.04$  and  $0.62 \pm 0.04$ <sup>23</sup>; in *Nd<sub>2-x</sub>Ce<sub>x</sub>CuO<sub>4</sub>* ( $x \sim 0.15$ )  $z\nu \sim 0.5$ <sup>24</sup>, and in amorphous Bi films  $z\nu = 0.7 \pm 0.2$ <sup>17,25</sup>. For transitions in amorphous bismuth films with varying thickness in a zero or constant normal magnetic field it was found  $z\nu = 1.4 \pm 0.2$ <sup>17,25</sup>. In Refs.<sup>[22,25]</sup>, in additional studies

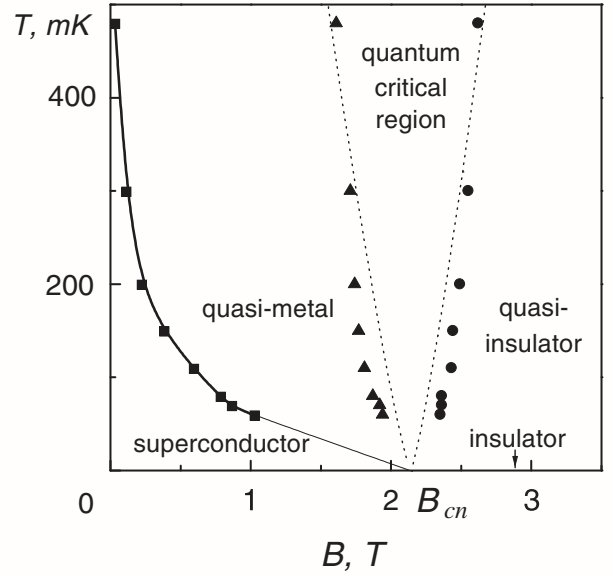


FIG. 7: Diagram of BKT phase transition in an amorphous *InO* film with thickness  $d = 20$  nm in  $(B, T)$  coordinates (according to the data of Ref. [20]). The magnetic field is oriented normally to the film surface. The solid line marks the boundary between the phases, and the dotted lines mark the boundaries of the quantum critical region.

of the electric field scaling for *MoGe* and *Bi* films the universal value  $z \approx 1.0$  of the dynamic critical index was obtained. The spread in the values of the product  $z\nu$  of indices in thin films was explained by the variations in the critical index  $\nu$ .

Let us use the value  $z\nu = 1.15 \div 1.22$ <sup>18,20</sup>, obtained in the studies of temperature scaling, for constructing the expected boundaries of the quantum critical region for quantum phase transition in the normal magnetic field. The corresponding boundaries are shown in Fig. 7 by dotted lines. As seen from the figure, the experimentally derived boundaries does not quite correspond to the theoretically expected one.

Besides the phase transition in amorphous *InO* films in the normal magnetic field, Gantmakher et al.<sup>20</sup> studied a transition from the superconducting to resistive state in the magnetic field oriented parallel to the film surface. The experimental dependencies of the *InO* film resistance on parallel magnetic field at different temperatures are shown in Fig. 6b. The isotherms  $R(B)$  intersect at the critical value  $B_{cp} \approx 5.4$  T of the magnetic field. The observed crossing of isotherms looks very much like evidence of a quantum phase transition between superconducting and insulating states of the film in the parallel field  $B = B_{cp}$ . In the critical magnetic field the resistance of the film is temperature independent and equal to  $R_{cp} \approx 5$  kOhm. Using the experimental data from

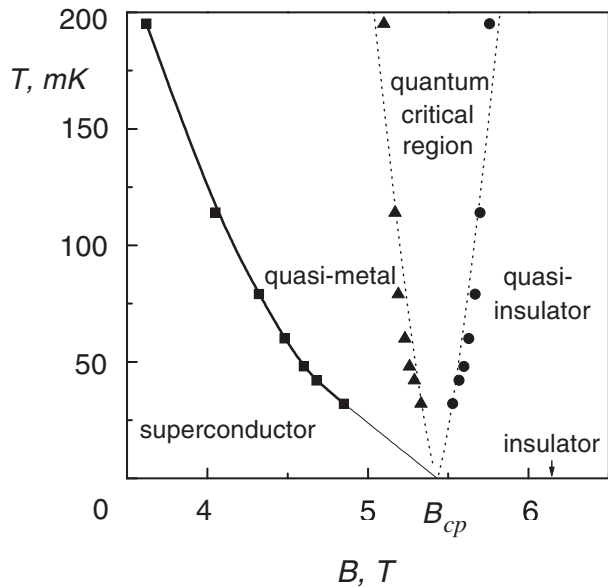


FIG. 8: Diagram of continuous phase transition in an amorphous *InO* film with thickness  $d = 20$  nm from superconducting to resistive state in  $(B, T)$  coordinates (according to the data of Ref. [20]). The magnetic field is oriented parallel to the film surface. The solid line marks the boundary between the phases, and the dotted lines mark the boundaries of the quantum critical region.

Fig. 6b, we find the phase transition boundary and the boundaries of the quantum critical region in the temperature range  $T = 32 \div 195$  mK by the method which has been described above for the transition in the normal magnetic field. The corresponding phase diagram for the case of parallel magnetic field is shown in Fig. 8.

Phase diagrams of the transition of an *InO* film from the superconducting to the insulating state in the parallel and the normal magnetic fields are strikingly similar. The temperature of transition to resistive state decreases with increase of magnetic field irrespective of its orientation. In the parallel magnetic field,  $T_c \propto (B_{cp} - B)^{1.78}$  (Fig. 8) which is close to  $T_{BKT} \propto |B - B_{cn}|^{2.49}$ , found in the normal orientation. In Ref.[20] it was shown that in the parallel magnetic field scaling exponent is equal to  $z\nu = 1.30$ . Knowing the product of critical indices, it is easy to draw an expected boundary of the quantum critical region (dotted lines in Fig. 8). As seen from the figure, the agreement between the expected critical region boundaries and the experimentally found points is distinctly better for the parallel field than for the normal one.

Hence, although the experiments on studying the superconductor- insulator phase transition in two-dimensional objects qualitatively confirm theoretical predictions<sup>19</sup>, they also reveal a number of problems. First, a BKT transition boundary has an unexpected

form. Second, the theory developed for the normal magnetic field and essentially using the fact of the normal field orientation, is unexpectedly formally suitable for describing results in the magnetic field parallel to the film surface.

### III. PHASE TRANSITIONS IN THE INTEGER QUANTUM HALL EFFECT REGIME

It is considered as evident that in the absence of a magnetic field a two-dimensional electron system is an insulator in arbitrary chaotic potential<sup>26</sup>. This statement, valid for the systems in which one can neglect electron-electron interaction, means that at zero temperature the conductance of a two-dimensional system starting from some, generally speaking, large size is exponentially decreasing with a further increase in a size of the system. In quantizing magnetic field with  $\omega_c \tau \gg 1$ , where  $\omega_c = eB/m^*$  is the cyclotron frequency, and  $\tau$  is the momentum relaxation time of electrons, the ground state of the system depends on the relation between the field strength and the density  $n_s$  of two-dimensional electrons, determined by the filling factor  $\nu^* = n_s/n_B$ , where  $n_B = eB/h$  is the number of magnetic flux quanta  $h/e$  per unit surface.

As it was experimentally found in 1980 in a silicon MOSFET<sup>27</sup>, in the vicinity of the integer filling factors the diagonal resistance  $R_{xx}$  takes a zero value, whereas the Hall component  $R_{xy}$  shows a set of quantized plateaus. In the vicinity of the half-integer filling factors,  $R_{xx}$  has maxima, and  $R_{xy}$  jumps from one plateau to another (Fig. 9). Such a behavior of the components of resistance tensor, known as integer quantum Hall effect (IQHE), was interpreted as the existence of a number of insulating phases with zero dissipative conductivity and quantized Hall conductivity separated by metallic states<sup>28</sup>. Experimentally, it is hard to proof the exact  $\sigma_{xy}$  quantization, because a simple inversion of the resistance tensor assumes a uniform current flow, whereas under conditions of the quantum Hall effect a significant part of the current flows near the sample edge<sup>29</sup>.

Consideration of IQHE as consequence of quantum phase transitions in the strong magnetic field<sup>28,30</sup> raises two principal questions: the first about the system behavior at zeroing of magnetic field, and the second on the detailed description of the transition region between quantum plateaus. The first question was theoretically considered in Ref.[31], where a chain of quantum phase transitions with quantized  $\sigma_{xy}$  values was predicted in the region of classically weak magnetic fields. Although the proposed picture, known as 'floating of extended states', has a number of indirect experimental confirmations<sup>32,33,34</sup>, there remain doubts about the possibility of realizing such a chain in samples of reasonable size at reasonable temperatures<sup>35</sup>. Below we discuss available experimental information regarding the second question.

Let us choose, as an example, a two-dimensional elec-

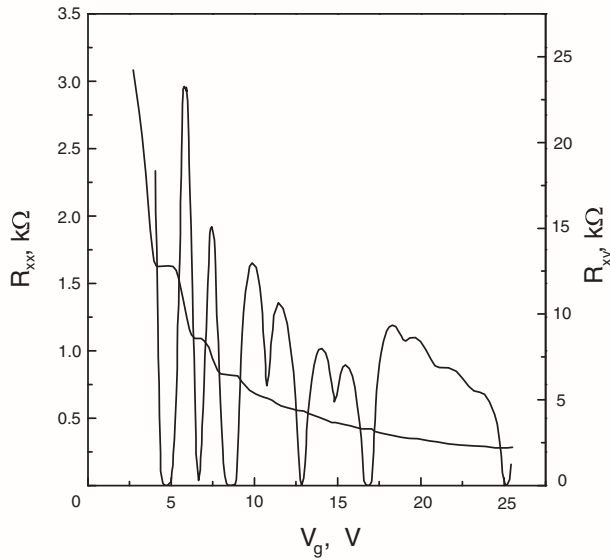


FIG. 9: Discovery of the integer quantum Hall effect in the two-dimensional electron system in a silicon MOSFET<sup>27</sup>. For the first time, the horizontal plateaus in the Hall resistance  $R_{xy}$  and corresponding minima of magnetoresistance  $R_{xx}$  at the temperature  $T = 1.5$  K were observed. On the horizontal axis, the values of the gate voltage  $V_g$ , which changes the concentration  $n_s$  of the carriers and, correspondingly, the filling factor in the constant magnetic field of 18 T, are plotted.

tron system in the long-period chaotic potential with the characteristic size  $l_0 \gg l_B$  in the plane, where  $l_B$  is the magnetic length<sup>36</sup>. The energy spectrum of an ideal system of noninteracting electrons in the magnetic field is presented by a set of delta functions ordered along the energy axis in accordance with the values of cyclotron energy  $\hbar\omega_c$  and the spin splitting energy  $E_s$  (Fig. 10, b). A long-period chaotic potential causes the inhomogeneous broadening of each of quantum levels (Fig. 10, c) so that at each level only one state, corresponding to the percolation threshold, is delocalized. The other electrons are localized near some extremes of the chaotic potential. At the tuning of the carrier density or of the magnetic field, i.e. at the tuning of filling factor, the Fermi level sequentially crosses the bands of localized states in which  $\sigma_{xx} = 0$ , and  $\sigma_{xy}$  takes a quantized value  $i(e^2/h)$  ( $i$ -is an integer). Transition between insulating phases with different indices  $i$  occurs via the metallic phase corresponding to the coincidence of the Fermi level  $E_F$  with the energy of delocalized state  $E_i$ . The number  $i$  of delocalized states under the Fermi energy, determining the value of  $\sigma_{xy}$ , changes by one and the dissipative conductivity shows a sharp peak.

In the symmetric potential at zero temperature, the condition  $E_F = E_i$  corresponds to the critical filling factor  $\nu_{ci}^* = i - 1/2$ . When approaching the critical filling

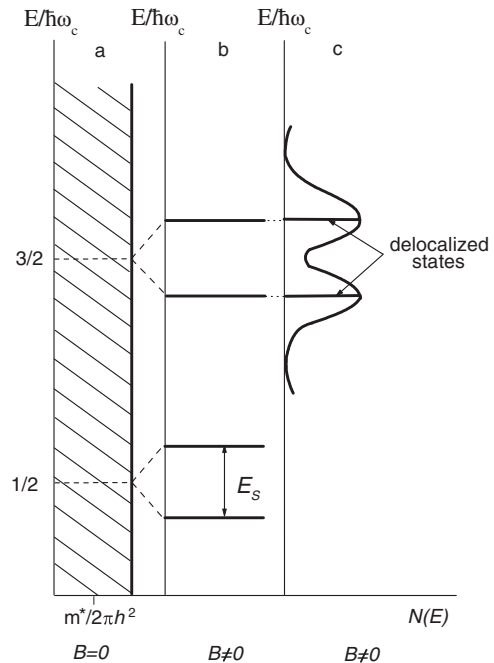


FIG. 10: Dependence of the density of states of a two-dimensional system of noninteracting electrons on energy: (a) in the absence of a magnetic field; (b) in the absence of scattering by chaotic potential, and (c) with a finite magnetic field and scattering.

factor, a localization length of the electrons at the Fermi level tends to infinity as  $\xi \propto |E_F - E_i|^{-\nu} \propto |\nu^* - \nu_{ci}^*|^{-\nu}$ . At a finite temperature one expects a gradual change in Hall conductance and a broadening of the dissipative conductance peaks in the quantum critical region of the transition between two insulating phases. The scaling parameter is a ratio of the temperature-assigned coherence length  $L_{in}(T) \propto T^{-p/2}$  (Ref.[37]) to the localization length of carriers at the Fermi-level:

$$u = (L_{in}(T)/\xi(\nu^*))^{1/\nu} \propto |\nu^* - \nu_{ci}^*| T^{-p/2\nu}. \quad (3)$$

In the quantum critical region, the components of the conductance tensor  $\sigma_{\alpha\beta}$  or conventionally measured in experiments resistivity tensor  $\rho_{\alpha\beta}$ , are expected to be functions of the scaling parameter  $u$ .

The  $m$ th order derivatives of kinetic characteristics taken at critical point depend on the temperature according to a power law

$$(\partial^m \rho(\nu^*)_{\alpha\beta} / \partial \nu^{*m})_{\nu^* = \nu_{ci}^*} \propto T^{-mp/2\nu}. \quad (4)$$

As follows from Refs.[28,30], the above described properties are valid for an arbitrary electron system in an arbitrary chaotic potential, if at each quantum level there exists one delocalized state with infinite localization length.

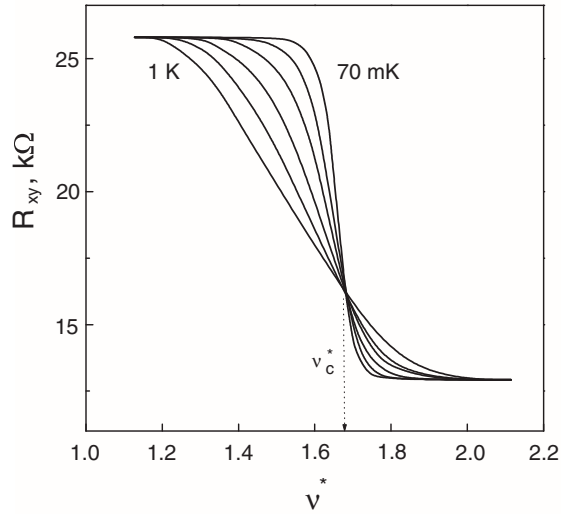


FIG. 11: Integer quantum Hall effect in the two-dimensional hole system  $Si/Si_{0.87}Ge_{0.13}$  (Ref.[<sup>38</sup>]). Dependencies of the Hall resistance  $R_{xy}$  on the filling factor  $\nu^*$  at the temperatures 70, 190, 330, 500, 700 and 1000 mK are shown. The arrow marks the critical value of the filling factor corresponding to a quantum phase transition between the states of a Hall insulator with  $i=2$  and  $i=1$ .

As an example, let us consider the phase transitions between the Hall insulators in the two-dimensional hole system  $Si/Si_{0.87}Ge_{0.13}$ <sup>38</sup>. Experimental dependencies of the Hall resistance of such a system on the filling factor are shown in Fig. 11 for different temperatures. The temperature-independent value of Hall resistance  $R_{xy} \approx 16$  kOhm corresponds to the critical filling factor  $\nu_c^* \approx 1.68$  for a quantum phase transition between Hall insulators with  $i=1$  and  $i=2$ . In insulating states with  $i=1$  and  $i=2$  Hall resistances  $R_{xy}$  are equal to  $h/e^2 \approx 26$  kOhm and  $h/2e^2 \approx 13$  kOhm, respectively.

Based on the data presented in Fig. 11 it is possible to construct a phase diagram similar to those shown in Fig. 7 and Fig. 8. Deviation of the Hall resistance from the quantized values  $h/ie^2$  corresponds to the metallic state of the system, which is separated from the insulating states by the phase boundaries, shown by solid lines in Fig. 12. The boundaries of quantum critical region  $\nu^*(T)$  can be determined through coincidence of the Hall resistance, measured at the maximum temperature of experiment  $T = T_{max}$ , with Hall resistance at  $T$ , after normalizing of the resistance according to  $R_{xy}(\nu^*) = R_{xy}^{norm}((\nu^* - \nu_c^*) * (T_{max}/T)^{p/2\nu})$ . The thus determined boundaries of the quantum critical region are marked in Fig. 12 by rectangles.

Motion along the horizontal line at constant temperature in Fig. 12 displaces the Fermi level from one band of

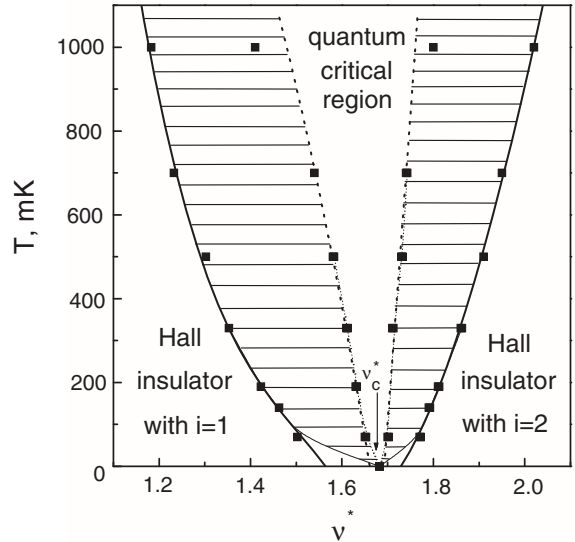


FIG. 12: Diagram of continuous phase transition between the states of a Hall insulator with  $i=1$  and  $i=2$  through the thermally disordered phase with metallic conductance (according to the data of Ref.[<sup>38</sup>]). Solid lines are the lines of phase transitions, dashed lines show the boundaries of the quantum critical region. Horizontal hatching marks the portion of the phase diagram corresponding to the thermally disordered phase with metallic conductance.

localized states to another one while crossing the delocalized state with infinite localization length. This motion corresponds to sequence of phase transitions from the insulating state  $i=1$  with Hall conductance  $\sigma_{xy} = e^2/h$  to the metallic state, and then to the new insulating state with  $i=2$ .

It was shown in Refs.[<sup>38,39</sup>] that for  $Si/Si_{0.87}Ge_{0.13}$  structures in the quantum critical region, the scaling relations (3) are really fulfilled with exponent  $k = 0.70 \pm 0.05$  for the transition between Hall insulators with  $i=1, i=2$  and with exponent  $k = 0.68 \pm 0.05$  for the transition between  $i=0$  and  $i=1$ . The analysis of experimental data was based on the assumption that all phase boundaries depicted in Fig. 12 will, on decreasing temperature, shrink into one point as shown by thin solid line and by dotted line in the figure. This assumption corresponds to the existence of only one delocalized state with infinite localization length at each of the quantum levels and can be substantiated only for noninteracting electrons in the long-period chaotic potential.

It appears natural to extrapolate the phase boundaries to zero temperature according to the experimentally established law which is, as seen from Fig. 12, close to the linear one. If such an extrapolation is correct, one should come to a conclusion on the finiteness of the band width of metallic state at zero temperature and, correspondingly, on the existence of two quantum phase transitions



in the intervals between insulating phases. Although the experimental evidence for the finite bandwidth of metallic state at zero temperature was found in a number of papers<sup>40,41,42,43</sup>, in none of them was performed a scaling analysis assuming the existence of two successive quantum phase transitions.

Following the pioneering work by Wei et al.<sup>44</sup>, an analysis of the experimental data assuming one extended state at the quantum level was done for two-dimensional systems  $InGaAs/InP$ <sup>45,46,47,48,49</sup>,  $AlGaAs/GaAs$ <sup>50,51</sup>, and  $GeSi/Ge$ <sup>52</sup>. In all these works, the exponent was equal to  $k = 0.42 \div 0.46$ . In Ref.<sup>[53]</sup>, the value of  $k = 0.57$  for transitions between the Hall insulators with  $i=1$  and  $i=0$  in the system  $InGaAs/InP$  was obtained. For transitions between the spin-degenerate insulating states in IQHE, a value approximately two times less,  $k \approx 0.2$  was found<sup>45,46</sup>. In experiments involving observation of IQHE in Si-MOSFET<sup>54</sup> and two-dimensional  $AlGaAs/GaAs$  systems, differing in the type and concentration of the dopant<sup>55</sup>, a dependence of the value of  $k$  on the number of the Landau level, carrier mobility and doping parameters was observed.

The spread in values of the scaling exponent is described by the difference in the mechanisms of inelastic electron scattering in various systems, which determine the value of the exponent  $p$  in the temperature dependence of the coherence length<sup>39</sup>, or by transitions belonging to different classes of universality<sup>47</sup>. The principal question on the bandwidth of the delocalized states, especially in systems with distinct effects of electron-electron interactions, escaped the attention of a majority of researchers.

#### IV. METAL-INSULATOR TRANSITION IN TWO-DIMENSIONAL SYSTEMS

Is it possible to observe a metal-insulator transition in a two-dimensional system in the limit of a zero magnetic field? Thirty five years ago there was no doubt about the answer: the transition is possible, and this is the Mott-Anderson transition. The publication of the theoretical paper Ref.<sup>[26]</sup> in 1979 radically changed the answer to this question. The authors of Ref.<sup>[26]</sup> employed a scaling approach to an analysis of the conductance of systems in the approximation of noninteracting carriers. According to the scaling hypothesis, a logarithmic derivative of dimensionless conductance  $g = 2\hbar G/e^2$  with respect to the system size  $L$  at zero temperature is a function only of the conductance itself. For two-dimensional systems in the absence of spin-orbit interaction, this derivative is negative in the whole range of values of dimensionless conductance. This means that with unlimited growing size of the system its conductance is continuously decreasing, i.e., a two-dimensional system of infinite size is, at zero temperature, in an insulating state with zero conductance independent of how large the initial conductance of the finite system was. Electron-electron inter-

action in the 'dirty' limit additionally enhances the localization of carriers<sup>56</sup>. A theory of quantum corrections (TQC) to conductance<sup>26,56,57,58,59,60,61</sup> that considers a phenomenon of weak localization and electron-electron interactions in disordered systems confirmed the asymptotic form of the scaling function at large values of conductance.

The following two almost complete decades can be named a time of triumph of TQC. This theory allowed the explanation and classification of the experimentally derived low-temperature anomalies in kinetic effects, in particular, negative magnetoresistance and logarithmic temperature dependence of the conductance of 'dirty' semiconductor heterostructures with two-dimensional electron or hole gas. The first observations of the TQC-predicted logarithmic dependence of conductance on temperature in Si-MOSFET were made in Refs.<sup>[62,63]</sup>. The experimentally established negative magnetoresistance in Si-MOSFET<sup>64,65,66,67</sup> was also analyzed from the TQC point of view. Characteristic sizes of the self-crossing trajectories, phase relaxation time of the electron wave function due to electron-electron and electron-phonon collisions, and the electron-electron coupling constant in the diffusive channel were determined. Mechanisms of the energy relaxation of electrons in classically weak and quantizing magnetic fields were also identified<sup>68</sup>. Thus, the experiments carried out in 1980s showed that TQC provides a sufficiently complete description of the low-temperature galvanomagnetic and kinetic effects in weakly disordered two-dimensional systems. Hence, the question about the nature of the ground state of a two-dimensional electron system in a zero magnetic field was, for almost two decades, considered to have a unique answer: at absolute zero of temperature one should not expect anything but the insulating state.

Against the background of numerous experimental confirmations of the conclusions drawn in Ref.<sup>[26]</sup> concerning the insulating properties of the ground state of two-dimensional systems, studies of the conductance of Si-MOSFET with a high ( $3 \cdot 10^4 \text{ cm}^2/(\text{V}\cdot\text{s})$ ) electron mobility<sup>69,70</sup> had a revolutionary character. In Refs.<sup>[69,70]</sup>, the temperature dependence of the resistance of Si-MOSFETs with two-dimensional electron gas in the range of sufficiently low electron concentrations  $n_s \leq 10^{11} \text{ cm}^{-2}$  was measured. Structures having electron concentrations  $\leq 10^{11} \text{ cm}^{-2}$  demonstrated a usual, for localized states, negative derivative  $dR/dT < 0$  of the resistance with respect to the temperature. However, at a certain critical concentration  $n_c \approx 10^{11} \text{ cm}^{-2}$ , the resistance of MOSFETs took an approximately temperature-independent value  $R \sim 2\hbar/e^2$ . An even more unexpected fact was a sharp decrease of the resistance with decreasing temperature in the structures with electron concentration  $n_s > n_c$ , which was observed down to the lowest experimentally reachable temperatures of 200 mK in the absence of any signs of electron localization (Fig. 13). The concentration  $n_c$  corresponding to a change in the sign of the derivative  $dR/dT$ , varied widely from sam-

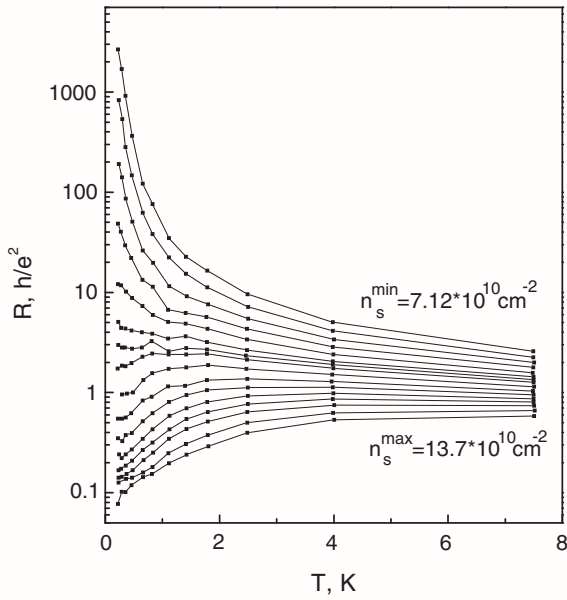


FIG. 13: Temperature dependencies of the resistance of Si-MOSFET with a concentration of two-dimensional electrons changing in the range  $7.12 \cdot 10^{10} \div 13.7 \cdot 10^{10} \text{ cm}^{-2}$  in a zero magnetic field<sup>70</sup>.

ple to sample, depending on the disorder in the electron system under investigation. A similar change in the sign of the derivative  $dR/dT$ , corresponding to the critical carrier concentration  $n_c(p_c)$ , was subsequently found in *AlGaAs/GaAs* heterostructures with two-dimensional electron<sup>71,72</sup> and hole<sup>73,74,75,76,77,78,79,80</sup> gas, quantum wells *AlAs* with two-dimensional electron gas<sup>81</sup>, as well as quantum *SiGe* wells with electron<sup>82</sup> and hole<sup>83,84</sup> gas. However, the temperature dependence of the resistance of these low-dimensional systems in the temperature range  $T < 1\text{K}$  turned out to be much less than that in silicon MOS structures (Fig. 14).

In the vicinity of critical carrier concentration, the resistance of MOSFETs showed the scaling with respect to temperature:

$$R(T, n_s) = f_1(|n_s - n_c|/T^{1/z\nu})$$

and electric field strength

$$R(E, n_s) = f_2(|n_s - n_c|/E^{1/(z+1)\nu})$$

with the exponents  $z = 0.8 \pm 0.1$ , and  $\nu = 1.5 \pm 0.1$ <sup>70,85</sup>.

The product of critical indices in Si-MOSFETs was equal to  $z\nu = 1.4 \div 1.7$ <sup>86</sup>. In experiments studying the low-temperature transport in Si-MOSFET with varying peak mobility, a dependence of the  $z\nu$  on the momentum relaxation time of electrons and critical concentration  $n_c$  has been observed<sup>87</sup>. In *AlGaAs/GaAs* heterostructures with two-dimensional electron gas, the analysis of scaling in temperature and electric field allowed the determination of the critical indices  $z = 1.4 \pm 1.0$  and  $\nu = 1.9 \pm 0.9$ <sup>72</sup>. In *AlGaAs/GaAs* with p-type conductance, the product of critical indices equals to  $z\nu =$

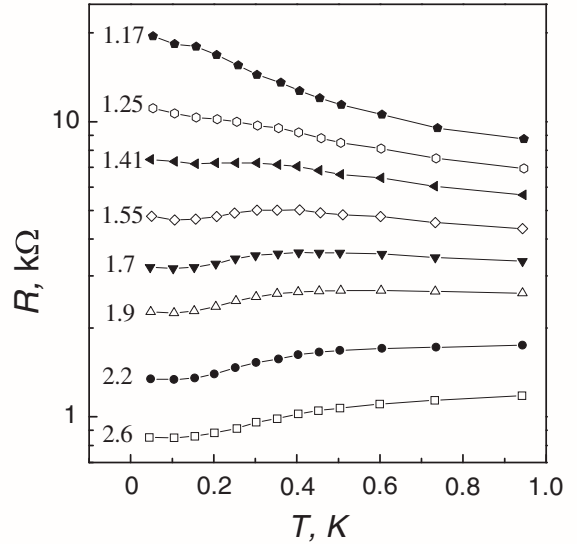


FIG. 14: Temperature dependencies of the resistance of *GaAs/AlGaAs* heterostructure with a concentration of two-dimensional holes varying in the range  $1.17 \cdot 10^{10} \div 2.6 \cdot 10^{10} \text{ cm}^{-2}$  in a zero magnetic field<sup>79</sup>.

$7.0 \pm 1.5$  and  $z\nu = 3.8 \pm 0.4$  for systems with a concentration of two-dimensional holes  $p > p_c$  and  $p < p_c$ , correspondingly<sup>74</sup>. In *SiGe* quantum wells involving two-dimensional electron gas with a concentration  $n_s < n_c$  the product of critical indices is equal to  $z\nu = 1.6 \pm 0.2$ <sup>82</sup>. For two-dimensional hole gas in *SiGe* quantum wells, the values of the product of critical indices obtained by different authors are equal to  $z\nu = 1.6 \div 2$ <sup>83</sup> and  $z\nu = 2.24 \pm 0.20$ <sup>84</sup>.

Could one consider a transition between the regimes with  $dR/dT < 0$  and  $dR/dT > 0$ , observed at finite temperatures, as a manifestation of the quantum phase transition of a two-dimensional system from the metallic to the insulating state in a zero magnetic field? This question should, first of all, be solved with respect to Si-(100) MOSFET. There are a number of reasons for such a conclusion. A change in the sign of the low-temperature derivative  $dR/dT$  at some critical concentration in Si-MOSFET offers an experimental fact that was reliably established by independent groups of researchers<sup>69,70,85,86,87,88,89</sup>.

In other systems, for example, in *AlGaAs/GaAs* and *SiGe* with two-dimensional electrons or holes, the temperature dependence of conductance on 'metallic' side of phase transition is much more weak as compared to the Si-MOSFET (see Figs. 13, and 14). Further cooling of these systems results in, at first, saturation of some (previously 'metallic') temperature dependencies of resistance, and then their transformation to the regime with  $dR/dT < 0$ . Such an effect was observed

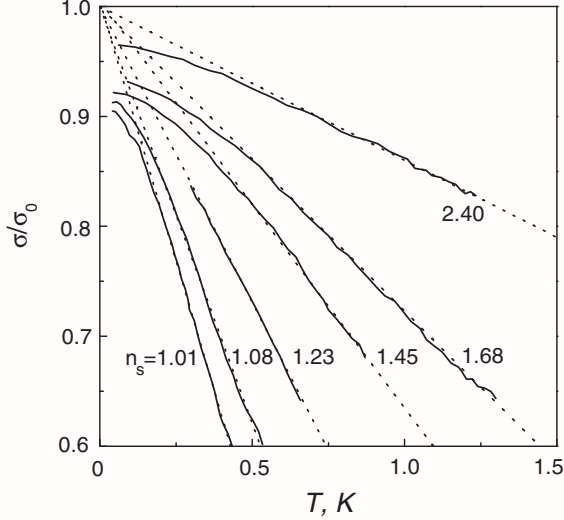


FIG. 15: Temperature dependencies of the normalized conductance of Si-MOSFET with the concentration of two-dimensional electrons varying in the range  $1.01 \cdot 10^{11} \div 2.4 \cdot 10^{11} \text{ cm}^{-2}$  in a zero magnetic field<sup>93</sup>. The dashed lines show a linear extrapolation of the temperature dependence of conductance to the limit of absolute zero of temperature.

in *AlGaAs/GaAs* heterostructures with two-dimensional electron<sup>72</sup> and hole<sup>79</sup> gas, as well as for two-dimensional holes in *SiGe*<sup>90</sup> and for two-dimensional electron gas of Si-MOSFET for vicinal orientations of the interface between *Si* and *SiO<sub>2</sub>*<sup>91</sup>.

In numerous experiments on Si-MOSFET<sup>69,70,85,86,87,88,89</sup> it was established that the critical carrier concentration corresponding to the change in the sign of the derivative  $dR/dT$  is determined by the quality of the sample. Therefore, the scaling of the dependencies  $R(T)$  in the main part of investigated samples should be considered as being occasional<sup>12</sup>. However, an anomalously sharp growth of the conductance with decreasing temperature cannot be explained within classical Drude theory. A giant change in the conductance can be caused by the change of the screening properties of a two-dimensional system<sup>92</sup> at a sharp reduction of the Fermi energy.

In the new experimental works<sup>88,93</sup>, the temperature dependence of the conductance of Si-MOSFET with the mobility of two dimensional electrons of the order of  $\sim 3 \cdot 10^4 \text{ cm}^2/(\text{B}\cdot\text{c})$ , in which a change in the sign of the derivative  $dR/dT$  corresponds to minimal critical electron density, was investigated in the range of ultra-low temperatures down to  $\approx 30 \text{ mK}$ . Structures with a concentration of two-dimensional electrons above the critical one showed a rapid linear growth of the normalized conductance  $\sigma(T)/\sigma_0$  with decreasing temperature in a suffi-

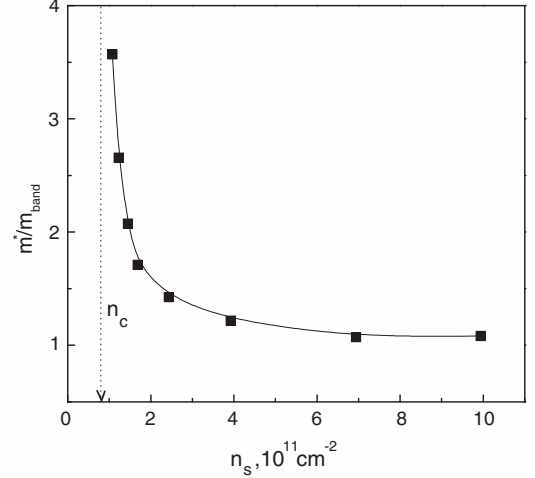


FIG. 16: Normalized effective mass as a function of electron density in Si-MOSFET with peak mobility  $3 \cdot 10^4 \text{ cm}^2/(\text{V}\cdot\text{s})$ <sup>93</sup>;  $m_{\text{band}} = 0.19m_e$ , where  $m_e$  is the mass of a free electron.

ciently wide temperature range (Fig. 15). Interpretation of the experimentally found linear temperature dependence in terms of Ref.<sup>[94]</sup> revealed a strong increase of the effective mass in Si-MOSFET, when the electron density approaches the value of  $0.8 \cdot 10^{11} \text{ cm}^{-2}$ , which practically coincided with  $n_c$  in the best studied samples<sup>93</sup>. Such a behavior of the cyclotron mass was confirmed in independent experiment<sup>95</sup> on the measurement of the temperature dependence of Shubnikov -de Haas oscillations. An analysis of the experimental data, analogous to that in Ref.<sup>[93]</sup>, but performed in the opposite limit with respect to the ratio of the valley splitting energy to temperature and using evidence of other experimental groups and samples from other sources<sup>96,97</sup>, confirmed the universality of the  $m^*(n_s)$  curve (Fig. 16).

As has already been mentioned, a conclusion to be made from recent experimental findings should be that a change in the sign of the derivative  $dR/dT$  at some concentration cannot, analogously to the conductance scaling, be considered as convincing evidence of a disorder driven quantum phase transition. The critical concentration  $n_c$ , corresponding to a change in a sign of the derivative  $dR/dT$  varies from one sample to another. However, the concentration  $n_c^*$  extracted from the divergence of the effective mass most probably takes a universal value or changes weakly from sample to sample. For the best samples, a negative magnetoresistance effect<sup>98</sup> disappears in the vicinity of this concentration. If a quantum phase transition in Si-MOSFET exists, one should think that  $n_c^*$  is precisely the quantum phase transition point. Such a phase transition is a property of pure, rather than disorder-

dered, two-dimensional systems with strong interparticle interactions, in particular, of the most perfect MOSFETs with a low electron concentration<sup>99</sup>.

## V. CONCLUSIONS

In many experimental studies of the quantum phase transitions in two-dimensional systems, the emphasis is, in our opinion, put on the facts that confirm the theory. The facts that are difficult to interpret within theoretical schemes are silently ignored. The full phase diagrams, similar to that shown in Fig. 1, have been, to the best of our knowledge, for the first time constructed from experimental data only in the present review (see Figs. 7, 8, 12).

A law describing the boundary of the quantum critical region can be determined from experiment and exploited for an independent control of the scaling relations. This possibility of independent control was, however, never used in the analysis of experimental data.

Therefore, existing theoretical ideas that successfully predicted and explained a number of experimental observations can hardly be currently considered as having been confirmed experimentally.

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